CEP8060L/CEB8060L

PRELIMINARY

N-Channel Logic Level Enhancement Mode Field Effect Transistor

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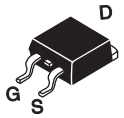
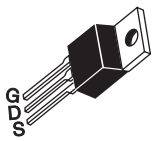
FEATURES

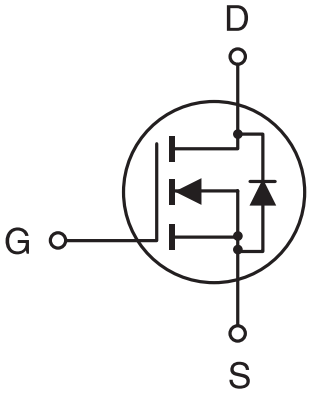
- 60V , 80A , $R_{DS(ON)}$=9.0mΩ @V_{GS}=10V.
  $R_{DS(ON)}$=12.0mΩ @V_{GS}= 5V.
- Super high dense cell design for extremely low $R_{DS(ON)}$.
- High power and current handling capability.
- TO-220 & TO-263 package.



CEB SERIES
TO-263(DD-PAK)



CEP SERIES
TO-220



ABSOLUTE MAXIMUM RATINGS (Tc=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous	I_D	80	A
-Pulsed	I_{DM}	225	A
Drain-Source Diode Forward Current	I_S	80	A
Maximum Power Dissipation @Tc=25°C	P_D	150	W
Derate above 25°C		1	W/°C
Operating and Storage Temperature Range	T_J, T_{STG}	-65 to 175	°C

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62.5	°C/W

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ELECTRICAL CHARACTERISTICS (T_C=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_D=250μA	60			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=60V, V_{GS}= 0V			25	μA
Gate-Body Leakage	I_{GSS}	V_{GS}=±20V, V_{DS}=0V			±100	nA
ON CHARACTERISTICS[a]						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D= 250μA	1		2	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}= 10V, I_D = 37.5A			9	mΩ
		V_{GS}= 5V, I_D= 37.5A			12	mΩ
On-State Drain Current	$I_{D(ON)}$	V_{GS}= 5V, V_{DS}= 10V	60			A
Forward Transconductance	g_{FS}	V_{DS}= 10V, I_D= 37.5A		15		S
DYNAMIC CHARACTERISTICS[b]						
Input Capacitance	C_{ISS}	V_{DS}=25V, V_{GS}= 0V f =1.0MHz		3230	4200	pF
Output Capacitance	C_{OSS}			1230	1600	pF
Reverse Transfer Capacitance	C_{RSS}			615	800	pF
SWITCHING CHARACTERISTICS[b]						
Turn-On Delay Time	$t_{D(ON)}$	V_{DD} = 30V, I_D =75A, V_{GS}= 5V R_{GEN} = 10Ω		20	40	ns
Rise Time	t_r			460	600	ns
Turn-Off Delay Time	$t_{D(OFF)}$			125	150	ns
Fall Time	t_f			210	400	ns
Total Gate Charge	Q_g	V_{DS} =48V, I_D =75A, V_{GS} =5V		61	115	nC
Gate-Source Charge	Q_{gs}			15		nC
Gate-Drain Charge	Q_{gd}			18		nC

ELECTRICAL CHARACTERISTICS (T_C=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
DRAIN-SOURCE DIODE CHARACTERISTICS [a]						
Diode Forward Voltage	V_{SD}	V_{GS} = 0V, Is =10A		0.86	1.2	V

Notes

a.Pulse Test:Pulse Width ≤300 μs, Duty Cycle ≤ 2%.

b.Guaranteed by design, not subject to production testing.

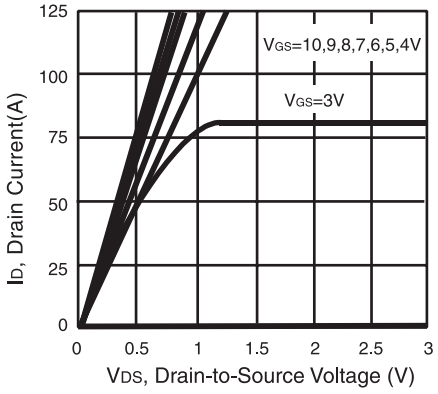

Figure 1. Output Characteristics

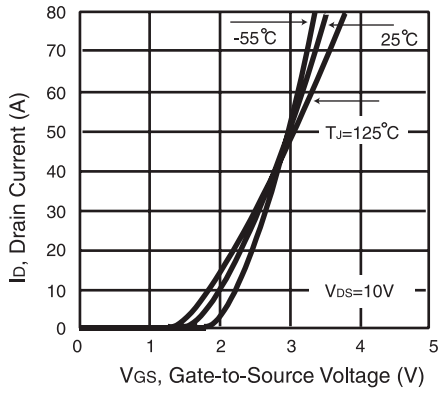

Figure 2. Transfer Characteristics

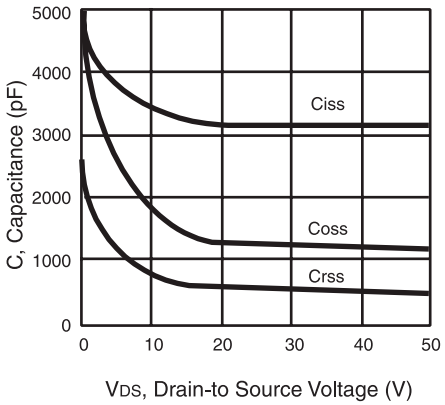

Figure 3. Capacitance

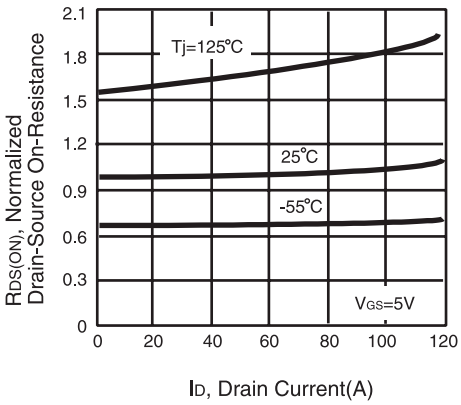

Figure 4. On-Resistance Variation with Drain Current and Temperature

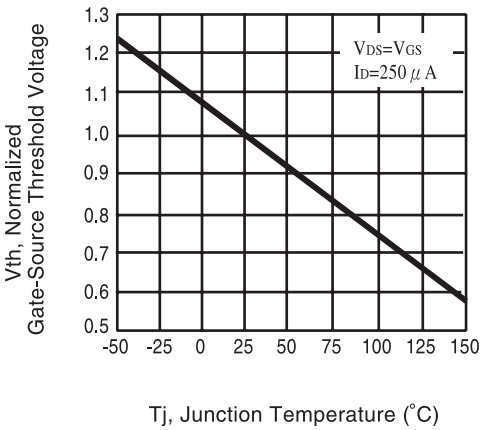

Figure 5. Gate Threshold Variation with Temperature

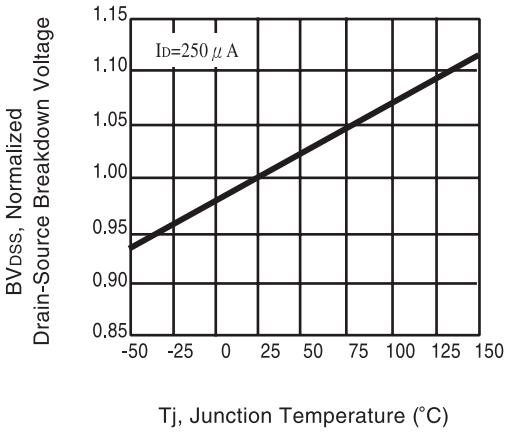

Figure 6. Breakdown Voltage Variation with Temperature

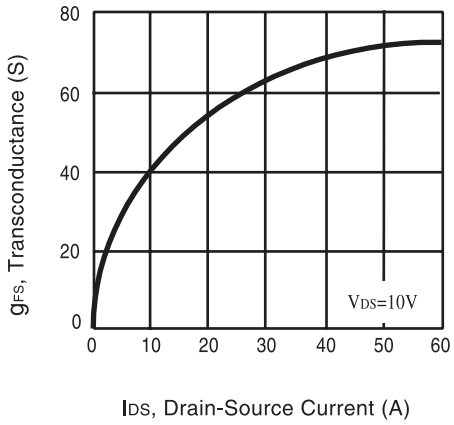

Figure 7. Transconductance Variation with Drain Current

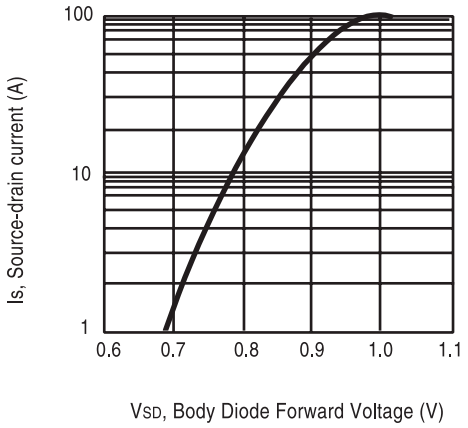

Figure 8. Body Diode Forward Voltage Variation with Source Current

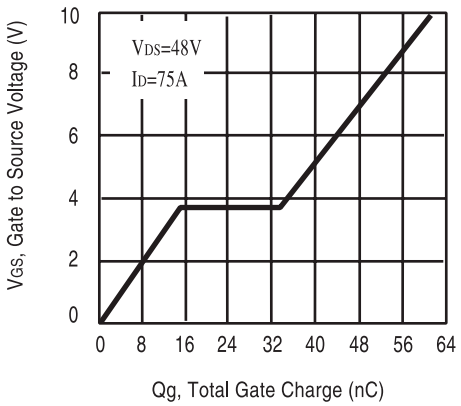

Figure 9. Gate Charge

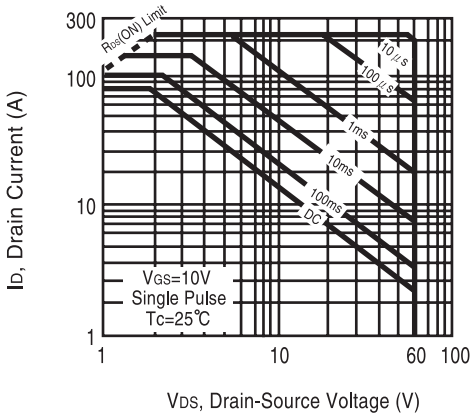

Figure 10. Maximum Safe Operating Area

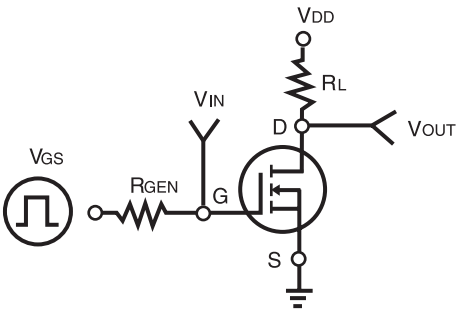

Figure 11. Switching Test Circuit

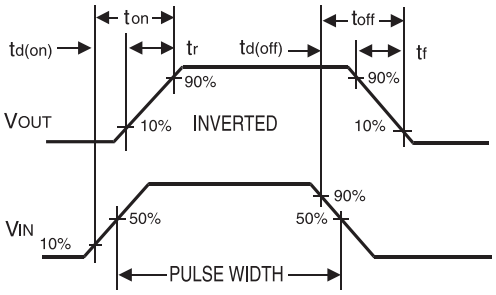

Figure 12. Switching Waveforms

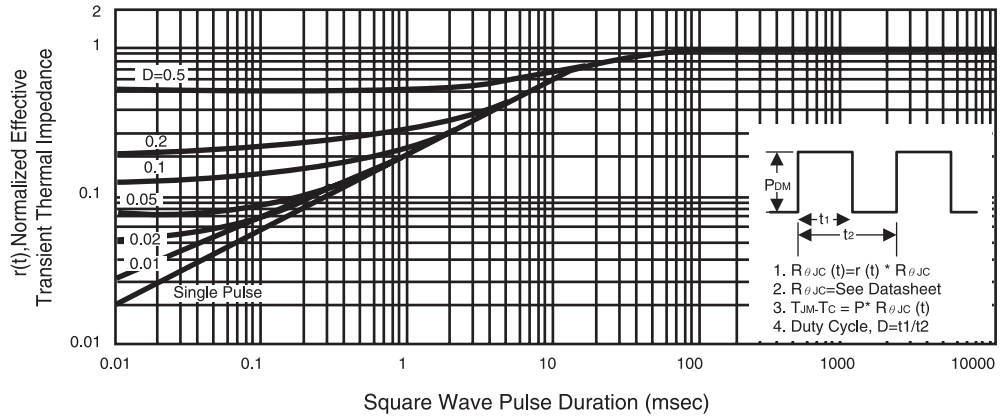

Figure 13. Normalized Thermal Transient Impedance Curve